## AS1345

18V, High Efficiency, DC/DC Step-Up

## Converter

## General Description

The AS1345 high efficiency DC/DC step-up converter contains an internal N -channel and an internal P-channel output isolation switch.
The device operates from a 2.9 V to 5.0 V supply and can boost voltages up to 18 V .

A hysteretic control scheme is used to provide the highest operating efficiency over a wide range of input and output load conditions. The internal MOSFET switches reduce the external component count and a high switching frequency allows the use of tiny surface mount components.

The AS1345 employ a factory set current limit to reduce ripple and external component size in low output current applications. With a 500 mA current limit the AS1345 is capable of providing $20 \mathrm{~mA} @ 18 \mathrm{~V}$ output.

Figure 1:
Available Products

| Devices | Peak Coil Current | Output |
| :---: | :---: | :---: |
| AS1345A | 100 mA | Adjustable or fixed |
| AS1345B | 200 mA | Adjustable or fixed |
| AS1345C | 350 mA | Adjustable or fixed |
| AS1345D | 500 mA | Adjustable or fixed |

Built-in safety features protect the internal switches and output components from fault conditions. Additional power-saving attributes include a very low quiescent current and a true shutdown mode.

Ordering Information and Content Guide appear at end of datasheet.

## Key Benefits \& Features

The benefits and features of AS1345, 18V, High Efficiency, DC/DC Step-Up Converter are listed below:

Figure 2:
Added Value of Using AS1345

| Benefits | Features |
| :---: | :---: |
| - Supports Lithium primary and re-chargeable batteries | - Input Voltage Range: 2.9 V to 5.0 V |
| - Supports a variety of end applications | - Adjustable Output Voltage Range: 5.0V to 18 V <br> - Output Current up to 40 mA |
| - Allows optimization of circuit depending on output power demands | - Inductor Peak Currents: 100, 200,350 and 500 mA |
| - Battery life improved | - 90\% Efficiency |
| - Battery supply isolated during shutdown | - True Shutdown |
| - Fault tolerant | - Short Circuit and Thermal Protection |
| - Small chipscale package | - Packages: <br> - 8-pin ( $2 \times 2 \mathrm{~mm}$ ) TDFN <br> - 8-bumps ( $1.570 \mathrm{~mm} \times 0.895 \mathrm{~mm}$ ) WL-CSP with 0.4 mm pitch |

## Applications

The AS1345 is ideal for:

- Small and low current demand LCD panels as well as for polymer LEDs (OLED)
- Cell phones, PDAs
- Readers
- Mobile terminals
- 3D shutter glasses


## Block Diagram

The functional blocks of this device are shown below:

Figure 3:
AS1345 Block Diagram


## Pin Assignment

Figure 4:
Pin Diagram (Top View)


Figure 5:
Pin Description

| Pin Number |  | Pin Name | Description |
| :---: | :---: | :---: | :---: |
| TDFN | WLP |  |  |
| 1 | A1 | VDD | Supply Voltage. Connect to a 2.9 V to 5.0 V input supply. Bypass this pin with a $10 \mu \mathrm{~F}$ capacitor. |
| 2 | A2 | EN | Enable Pin. Logic controlled shutdown input, 1.8V CMOS compatible; <br> 1 = Normal operation <br> $0=$ Shutdown <br> On request a $100 \mathrm{k} \Omega$ pull-down resistor can be enabled (factory set). |
| 3 | A3 | FB | Feedback Pin. Feedback input to the gm error amplifier. <br> For an adjustable output voltage connect a resistor divider to this pin. The output can be adjusted from 5.0 V to 18 V by: $\text { Vout }=\text { VREF } \times(1+\text { R2/R3 })$ <br> If the fixed output voltage version is used, connect this pin to Vout. |
| 4 | A4 | POK | POK. Open Drain Output. POK remains low while Vout is less than $90 \%$ of nominal Vout. Connect a $100 \mathrm{k} \Omega$ pull-up resistor from this pin to VdD. |
| 5 | B4 | SWIN | Shutdown Disconnect Switch In. Input pin of the internal P-channel MOSFET. |


| Pin Number |  | Pin Name |  |
| :---: | :---: | :---: | :--- |
| TDFN | WLP |  | Description |
| 6 | B3 | SWOUT | Shutdown Disconnect Switch Out. Output pin of the internal <br> P-channel MOSFET. Connect to power inductor and decouple to GND <br> with a 10 $\mu$ F low ESR ceramic capacitor. <br> When the input disconnect feature is not desired, SWOUT should be <br> connected to SWIN and VDD. |
| 7 | B2 | LX | Inductor. The drain of the internal N-channel MOSFET. Connect to <br> power inductor and to anode of a schottky diode. |
| 8 | B1 | GND | Ground |

## Absolute Maximum Ratings

Stresses beyond those listed in the table below may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in Electrical Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 6:
Absolute Maximum Ratings

| Parameter |  | Min | Max | Unit | Comments |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Electrical Parameters |  |  |  |  |  |
| VDD, SWIN, SWOUT to GND |  | -0.3 | 7 | V |  |
| LX, FB to GND |  | -0.3 | 20 | V |  |
| Input Current (latch-up immunity) |  | -100 | 100 | mA | JEDEC 78 |
| SWIN to SWOUT Current Limit |  |  | 1 | A |  |
| Electrostatic Discharge |  |  |  |  |  |
| Electrostatic Discharge HBM |  | $\pm 2$ |  | kV | MIL 883 E method 3015 |
| Temperature Ranges and Storage Conditions |  |  |  |  |  |
| Junction temperature |  |  | 110 | ${ }^{\circ} \mathrm{C}$ |  |
| Storage temperature range | WL-CSP | -55 | 125 | ${ }^{\circ} \mathrm{C}$ |  |
|  | TDFN | -55 | 150 | ${ }^{\circ} \mathrm{C}$ |  |
| Package thermal data | WL-CSP |  | 60 |  | Junction-to-ambient thermal resistance is very dependent on application and board-layout. In |
|  | TDFN |  | 97 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ | situations where high maximum power dissipation exists, special attention must be paid to thermal dissipation during board design. |
| Package body temperature | WL-CSP |  | 260 | ${ }^{\circ} \mathrm{C}$ | IPC/JEDEC J-STD-020 |
|  | TDFN ${ }^{(2)}$ |  |  |  | IPC/JEDEC J-STD-020 |
| Relative humidity non-condensing |  | 5 | 85 | \% |  |
| Moisture sensitivity level | WL-CSP | 1 |  |  | Represents an unlimited floor life time |
|  | TDFN | 1 |  |  | Represents an unlimited floor life time |

## Note(s):

1. The reflow peak soldering temperature (body temperature) specified is in accordance with IPC/JEDEC J-STD-020"Moisture/Reflow Sensitivity Classification for Non-Hermetic Solid State Surface Mount Devices".
2. The lead finish for Pb-free leaded packages is "Matte Tin" ( $100 \% \mathrm{Sn}$ ).

Electrical Characteristics
All limits are guaranteed. The parameters with Min and Max values are guaranteed by production tests or SQC (Statistical Quality Control) methods.

Figure 7:
$\mathbf{V}_{\text {DD }}=\mathbf{V}_{\text {SHDNN }}=\mathrm{V}_{\text {SWIN }}=3.7 \mathrm{~V}, \mathrm{~V}_{\text {OUT }}=15 \mathrm{~V}, \mathrm{CIN}=$ COUT $=10 \mu \mathrm{~F}$, Typical Values $@ \mathrm{~T}_{\text {AMB }}=25^{\circ} \mathrm{C}$ (unless otherwise specified)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| TAMB | Operating temperature range |  | -40 |  | 85 | ${ }^{\circ} \mathrm{C}$ |
| TJ | Operating junction temperature range |  | -40 |  | 110 | ${ }^{\circ} \mathrm{C}$ |
| Input |  |  |  |  |  |  |
| VDD | Supply voltage range | SWIN connected to VDD | 2.9 |  | 5.0 | V |
|  | Minimum startup voltage | VDD $=$ SWIN |  | 2.7 |  | V |
| VUVLO | VDD undervoltage lockout | VDD decreasing ( 50 mV Hysteresis) |  | 2.7 |  | V |
| Regulation |  |  |  |  |  |  |
| Vout | Adjustable output voltage range | External FB divider | 5 |  | 18 | V |
|  | Feedback voltage tolerance | Tolerance of FB resistors not included | -3 |  | 3 | \% |
|  | Fixed output voltage | Internal FB divider |  | 12 |  | V |
|  |  |  |  | 15 |  |  |
|  |  |  |  | 17 |  |  |
| VFb | Feedback voltage | For adjustable Vout only |  | 1.25 |  | V |
|  | Feedback input current |  |  | 10 | 1000 | nA |
|  | Line regulation | $\mathrm{VDD}=3.5 \mathrm{~V}$ to 3.7V |  | 200 |  | mV |
|  | Load regulation | VOUT $=15 \mathrm{~V}$, ILOAD $=0 \mathrm{~mA}$ to 5 mA |  | 50 |  | mV |
| $\eta$ | Efficiency | $\begin{aligned} & \mathrm{L}=22 \mu \mathrm{H}, \mathrm{VDD}=\mathrm{VSWIN}= \\ & 3.7 \mathrm{~V}, \text { VOUT }=15 \mathrm{~V}, \\ & \text { ILOAD }=10 \mathrm{~mA} \end{aligned}$ |  | 90 |  | \% |


| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Operating Current |  |  |  |  |  |  |
| ISHDN | Shutdown current @ VDD | Vshdnn $=0 \mathrm{~V}$ |  |  | 1 | $\mu \mathrm{A}$ |
|  | Shutdown current @ SWIN |  |  |  | 1 |  |
| lQ | Quiescent current | No switching, VFB $=1.5 \mathrm{~V}$ |  | 25 |  | $\mu \mathrm{A}$ |
| IdDLOAD | Load current | Vout $=15 \mathrm{~V}, \mathrm{ILOAD}=5 \mathrm{~mA}$ |  | 25 |  | mA |
| ILIMIT | Coil peak current limit | AS1345A |  | 100 |  | mA |
|  |  | AS1345B |  | 200 |  | mA |
|  |  | AS1345C |  | 350 |  | mA |
|  |  | AS1345D |  | 500 |  | mA |
| Switches |  |  |  |  |  |  |
| $\mathrm{R}_{\text {NMOS }}$ | NMOS resistance |  |  | 0.3 |  | $\Omega$ |
| $\mathrm{R}_{\text {PMOS }}$ | PMOS resistance |  |  | 0.15 |  | $\Omega$ |
| POK Output |  |  |  |  |  |  |
|  | POK output voltage 'low' | POK sinking 1mA |  | 0.01 | 0.2 | V |
|  | POK output voltage 'high' | POK leakage $1 \mu \mathrm{~A}$ | VDD |  | $\begin{aligned} & \text { VDD } \\ & -0.1 \end{aligned}$ | V |
|  | POK output high leakage current | $\mathrm{POK}=3.7 \mathrm{~V}$ |  |  | 1 | $\mu \mathrm{A}$ |
|  | POK threshold | Rising edge, referenced to Vout(Nom) |  | 90 |  | \% |
| Shutdown |  |  |  |  |  |  |
| VshDNH | SHDN input 'high' | $2.9 \mathrm{~V}<\mathrm{VDD}<5.0 \mathrm{~V}$, no load | 1.26 |  |  | V |
| VshdnL | SHDN input 'low' |  |  |  | 0.55 | V |
| ISHDN | SHDN input current |  | -1 |  | 1 | $\mu \mathrm{A}$ |
| Soft Start |  |  |  |  |  |  |
| IPRE | Pre-charge current |  |  | 100 |  | mA |
| Thermal Shutdown |  |  |  |  |  |  |
|  | Thermal shutdown |  |  | 150 |  | ${ }^{\circ} \mathrm{C}$ |
|  | Thermal shutdown hysteresis |  |  | 10 |  | ${ }^{\circ} \mathrm{C}$ |

## Typical Operating Characteristics

Vout $=15 \mathrm{~V}$

Figure 8:
Efficiency vs. IOUT; $\mathrm{V}_{\text {IN }}=2.7 \mathrm{~V}$, $\mathrm{I}_{\text {LIMIT }}=100 \mathrm{~mA}$


Figure 9:
Efficiency vs. IOUT; $\mathrm{V}_{\text {IN }}=2.7 \mathrm{~V}$, I ${ }_{\text {LIMIT }}=500 \mathrm{~mA}$


Figure 10:
Efficiency vs. $I_{\text {OUT }}{ }^{\circ} \mathrm{V}_{\text {IN }}=4.5 \mathrm{~V}, \mathrm{I}_{\text {LIMIT }}=100 \mathrm{~mA}$


Figure 11:
Efficiency vs. $I_{\text {OUT }} \mathrm{V}_{\text {IN }}=4.5 \mathrm{~V}, \|_{\text {LIMIT }}=500 \mathrm{~mA}$


Figure 12:
Efficiency vs. $\mathrm{V}_{\text {IN }}$; $\mathrm{I}_{\text {LOAD }}=5 \mathrm{~mA}$, $\mathrm{I}_{\text {LIMIT }}=100 \mathrm{~mA}$


Figure 13:
Efficiency vs. $\mathrm{V}_{\text {IN }} ; \|_{\text {LOAD }}=5 \mathrm{~mA} / 20 \mathrm{~mA}$, $\|_{\text {LIMIT }}=500 \mathrm{~mA}$


Figure 14:
$\mathrm{V}_{\text {OUT }}$ vs. I OUTi $\mathrm{V}_{\text {IN }}=2.7 \mathrm{~V}$, I LIMIT $=100 \mathrm{~mA}$


Figure 15:
$\mathrm{V}_{\text {OUT }}$ vs. $\mathrm{I}_{\text {OUT }} \mathrm{V}_{\text {IN }}=4.5 \mathrm{~V}$, I IIMIT $=100 \mathrm{~mA}$


Figure 16:
$\mathrm{V}_{\text {OUT }}$ vs. I OUT $\mathrm{V}_{\text {IN }}=4.5 \mathrm{~V}$, I LIMIT $=500 \mathrm{~mA}$


## Detailed Description

The AS1345 is a compact step-up DC/DC converters that operates from a 2.9 V to 5.0 V supply. Consuming only $25 \mu \mathrm{~A}$ of Quiescent current. These devices include an internal MOSFET switch with a low on-resistance. A true shutdown feature disconnects the battery from the load and reduces the supply current to $0.05 \mu \mathrm{~A}$ (typ). These DC/DC converters are available with either a fixed output or are adjustable up to 18 V . Four current-limit options are available: $100 \mathrm{~mA}, 200 \mathrm{~mA}, 350 \mathrm{~mA}$ and 500 mA .

Figure 17:
Typical Application Diagram


## Modes of Operation

The AS1345 features an advanced current-limited control scheme operating in hysteretic mode. An internal P-channel MOSFET switch connects VDD to SWIN to provide power to the inductor when the converter is operating. When the converter is shut down, this switch disconnects the input supply from the inductor (see Figure 17). To boost the output voltage an N-channel MOSFET switch turns on and allows current to ramp up in the inductor. Once this current reaches the current limit, the switch turns off and the inductor current flows through D1 to supply the output. The switching frequency varies depending on the load and input voltage and can be up to 10 kHz .

## Shutdown

Drive EN low to enter shutdown mode. During shutdown the supply current drops to $0.05 \mu \mathrm{~A}$ (typ), the output is dis-connected from the input, and LX enters a high impedance state. The capacitance and load at the output set the rate at which Vout decays. EN can be pulled as high as 6V regardless of the input and output voltages.

With a typical step-up converter circuit, the output remains connected to the input through the inductor and output rectifier, holding the output voltage to one diode drop below VDD when the converter is shutdown and allowing the output to draw power from the input.
The AS1345 features a True-Shutdown mode, disconnecting the output from the input with an internal P-channel MOSFET switch when shut down. This eliminates power draw from the input during shutdown mode.

## Start-up and Inrush Limiting

If the ENABLE pin is high, the AS1345 uses a multi-stage start-up sequence. With increasing supply voltage, first the power-on circuitry becomes active and some internal blocks are initiated. If the supply exceeds the under-voltage-lockout threshold (2.7V typ), the pre-charge-phase is initiated. The capacitor at the SWOUT pin is charged to VIN, and the capacitor at Vout is charged to VIN-VSD. During this phase the current is limited to 100 mA typical. After the completion of the pre-charge-phase, the AS1345 enters into switching mode. Here the specified current-limit $\mathrm{I}_{\text {PEAK }}$ is used. The circuit operates at maximum frequency until the desired Vout is reached. Then AS1345 switches to normal hysteretic operation mode.
If the load current is too high ( $>50 \mathrm{~mA}$ ) during the start-up-phase, the attainment of normal operation mode might be delayed or not done at all.

## Adjustable Output Voltage

The output voltage of the AS1345 is adjustable from 5.0 V to 18 V by using a resistor voltage-divider (see Figure 18 and Figure 19). Select R1 from $10 \mathrm{k} \Omega$ to $600 \mathrm{k} \Omega$ and calculate R 2 with the following equation:

Vout $=$ Vref (1 + R2/R3) (EQ1)
Where: $\operatorname{VREF}=1.25 \mathrm{~V}$
Vout can range from 5.0 V to 18 V
For best accuracy, ensure that the bias current through the feedback resistors is at least $2 \mu \mathrm{~A}$.

The AS1345 can also be used with a fixed output voltage. When using one of these parts, connect FB directly to the output (see Figure 20 and Figure 21).

For improved regulation speed and lower ripple C3 should be applied. For best ripple performance always the adjustable variant of the AS1345 together with C3 should be used. Other measures to reduce the ripple could be to select a low peak current $\mathrm{I}_{\text {PEAK }}$ and increase C4 and to decrease the value of L .

Figure 18:
AS1345 with Adjustable Output Voltage, with Output Disconnect


Figure 19:
AS1345 with Adjustable Output Voltage, without Output Disconnect


Figure 20:
AS1345 with Fixed Output Voltage, with Output Disconnect


Figure 21:
AS1345 with Fixed Output Voltage, without Output Disconnect


## Power OK Operation

If desired the POK functionality can be used. In this case a resistor R1 ( $\sim 100 \mathrm{k}$ ) has to be applied between the POK pin and VIN, because the POK output is an open drain type. If the POK functionality is not used the pin should be unconnected.

During shut-down the POK pin is high impedance to save current. Therefore it shows VIN if connected to VIN with a resistor or is floating otherwise. During start-up the POK goes to LOW. During normal operation it is usually HIGH but it goes to LOW if for some reason VOUT drops below $90 \%$ of the nominal output voltage.

## Thermal Shutdown

To prevent the AS1345 from short-term misuse and overload conditions the chip includes a thermal overload protection. To block the normal operation mode all switches will be turned off. The device is in thermal shutdown when the junction temperature exceeds $150^{\circ} \mathrm{C}$ typ. To resume the normal operation the temperature has to drop below $140^{\circ} \mathrm{C}$ typ. A good thermal path should be provided to dissipate the heat generated within the package, especially at higher output power. To dissipate as much heat as possible from the package into a copper plane with as much area as possible, it's recommended to use multiple vias in the printed circuit board.

Continuing operation in thermal overload conditions may damage the device, and therefore, is considered a bad practice.

## Inductor Selection

For best efficiency, choose an inductor with high frequency core material, such as ferrite, to reduce core losses. The inductor should have low $D C R$ ( $D C$ resistance) to reduce the $I^{2} R$ losses, and must be able to handle the peak inductor current without saturating. A $10 \mu \mathrm{H}$ to $22 \mu \mathrm{H}$ inductor with greater than 500 mA current rating and less than $500 \mathrm{~m} \Omega \mathrm{DCR}$ is recommended. When smaller peak currents are selected, the inductor current specification can be reduced accordingly.

Figure 22:
Recommended Inductors

| Part Number | Value | Current | Resistance | Size (ins) | Supplier |
| :---: | :---: | :---: | :---: | :---: | :---: |
| ELJLA100KF | $10 \mu \mathrm{H}$ | 600 mA | $0.71 \Omega$ | 1210 | Panasonic www.panasonic.com |
| ELJLA220KF | $22 \mu \mathrm{H}$ | 420 mA | $1.9 \Omega$ | 1210 |  |
| ELJPA100KF2 | $10 \mu \mathrm{H}$ | 400 mA | $0.35 \Omega$ | 1210 |  |
| ELJPA220KF2 | $22 \mu \mathrm{H}$ | 290 mA | $0.66 \Omega$ | 1210 |  |
| ELJPA100KF | $10 \mu \mathrm{H}$ | 240 mA | $0.5 \Omega$ | 1210 |  |
| ELJPA150KF | $15 \mu \mathrm{H}$ | 220 mA | $0.74 \Omega$ | 1210 |  |
| ELJPA220KF | $22 \mu \mathrm{H}$ | 185 mA | $1.15 \Omega$ | 1210 |  |
| ELJPC100MF3 | $10 \mu \mathrm{H}$ | 140 mA | $0.58 \Omega$ | 1008 |  |
| ELJPC220MF3 | $22 \mu \mathrm{H}$ | 100 mA | $1.22 \Omega$ | 1008 |  |
| LQH32PN100MNO | $10 \mu \mathrm{H}$ | 750 mA | $0.38 \Omega$ | 1210 | Murata Manufacturing Company www.murata.com |
| LQH32PN150MNO | $15 \mu \mathrm{H}$ | 600 mA | $0.57 \Omega$ | 1210 |  |
| LQH32PN220MNO | $22 \mu \mathrm{H}$ | 500 mA | $0.81 \Omega$ | 1210 |  |
| LQH3NPN100NGO | $10 \mu \mathrm{H}$ | 500 mA | $0.38 \Omega$ | 1212 |  |
| LQH3NPN150NGO | $15 \mu \mathrm{H}$ | 370 mA | $0.91 \Omega$ | 1212 |  |
| LQH3NPN220NGO | $22 \mu \mathrm{H}$ | 340 mA | $1.1 \Omega$ | 1212 |  |
| LQH2MCN100M52 | $10 \mu \mathrm{H}$ | 200 mA | $2.27 \Omega$ | 0806 |  |
| LQH2MCN150M52 | $15 \mu \mathrm{H}$ | 150 mA | $3.5 \Omega$ | 0806 |  |
| LQH2MCN220M52 | $22 \mu \mathrm{H}$ | 130 mA | $5.5 \Omega$ | 0806 |  |

## Capacitor Selection

The convertor requires three capacitors. Ceramic X5R or X7R types will minimize ESL and ESR while maintaining capacitance at rated voltage over temperature. The Vin capacitor should be $10 \mu \mathrm{~F}$. The Vout capacitor should be between $1 \mu \mathrm{~F}$ and $10 \mu \mathrm{~F}$. A larger output capacitor should be used if lower peak to peak output voltage ripple is desired. A larger output capacitor will also improve load regulation on Vout. See table below for a list of capacitors for input and output capacitor selection.

Figure 23:
Recommended Capacitors

| Part Number | Value | Voltage | TC Code | Size (ins) | Supplier |
| :---: | :---: | :---: | :---: | :---: | :---: |
| GRM31CR71E106KA12L | 10رF | 25 V | X7 | 1206 | Murata <br> Manufacturing <br> Company <br> www.murata.com |
| GRM31CR71C106KAC7L | 10رF | 16V | X7 | 1206 |  |
| GRM31CR71A106KA01L | 10رF | 10 V | X7 | 1206 |  |
| GRM21BR70J106KE76L | $10 \mu \mathrm{~F}$ | 6.3 V | X7 | 0805 |  |
| GRM31CR71E475KA88L | $4.7 \mu \mathrm{~F}$ | 25V | X7 | 1206 |  |
| GRM21BR71C475KA73L | $4.7 \mu \mathrm{~F}$ | 16 V | X7 | 0805 |  |
| GRM188R71E105KA12D | $1 \mu \mathrm{~F}$ | 25 V | X7 | 0603 |  |
| GRM188R71C105KA12D | $1 \mu \mathrm{~F}$ | 16V | X7 | 0603 |  |

## Schottky Diode Selection

The selection of the external diode depends on the application. If lout is very low most of the time, and Vout is high, select a diode with a low reverse current for best efficiency. For lower Vout and higher Iout, select a diode with a lower $V_{\text {FORWARD }}$ and $\mathrm{R}_{\text {FORWARD }}$.

Figure 24:
Recommended Diodes

| Part Number | Reverse <br> Voltage | Average Rectified Current | Forward Voltage | Reverse Leakage Current | Package | Supplier |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| MBR0540 | 40V | 500 mA | $\begin{gathered} 460 \mathrm{mV} \text { @ } \\ 500 \mathrm{~mA} \end{gathered}$ | $1 \mu \mathrm{~A} @ 20 \mathrm{~V}$ | SOD123 | Fairchild Semiconductor www.fairchildsemi.com |
| B140HW | 40V | 1000mA | $\begin{gathered} 460 \mathrm{mV} \text { @ } \\ 500 \mathrm{~mA} \end{gathered}$ | $\begin{gathered} 0.35 \mu \mathrm{~A} @ \\ 20 \mathrm{~V} \end{gathered}$ | SOD123 | Diodes Inc www.diodes.com |
| PMEG2010AEB | 20V | 1A | $\begin{gathered} 200 \mathrm{mV} \text { @ } \\ 500 \mathrm{~mA} \end{gathered}$ | $\begin{gathered} 320 \mu \mathrm{~A} @ \\ 20 \mathrm{~V} \end{gathered}$ | SOD523 | NXP Semiconductors www.nxp.com |
| CRS04 | 40V | 1A | $\begin{gathered} 450 \mathrm{mV} \text { @ } \\ 500 \mathrm{~mA} \end{gathered}$ | $\begin{gathered} 40 \mu \mathrm{~A} @ \\ 20 \mathrm{~V} \end{gathered}$ | 3-2A1A <br> (Toshiba) | Toshiba www.toshiba-compone nts.com |
| CRS06 | 20V | 1A | $\begin{gathered} 325 \mathrm{mV} @ \\ 500 \mathrm{~mA} \end{gathered}$ | $\begin{gathered} 250 \mu \mathrm{~A} @ \\ 20 \mathrm{~V} \end{gathered}$ | 3-2A1A <br> (Toshiba) |  |

## PCB Layout

Carefully printed circuit layout is important for minimizing ground bounce and noise. Keep the GND pin and ground pads for the input and output capacitors as close together as possible. Keep the connection to LX as short as possible. Locate the feedback resistors as close as possible to the FB pin and keep the feedback traces routed away from noisy areas such as LX.

EMI and overall performance quality are affected by the PCB layout. The high speed operation of the AS1345 demands careful attention to board layout. Stated performance will be difficult to achieve with careless layout. Figure 25 identifies the high current paths during an operation cycle involving the switching of the N -channel and P -channel internal switches. The current paths between SWIN, VIN, C1, C2, C4, L1, D1 and GND should be short and wide for lowest intrinsic resistive loss and lowest stray inductance.

A large ground pin copper area will help to lower the chip temperature. A multilayer board with a separate ground plane is ideal, but not absolutely necessary.

Figure 25:
AS1345 - Inductor Current Paths


Package Drawings \& Markings
The product is available in a 8-pin (2x2) TDFN and 8-bump ( $1.570 \mathrm{~mm} \times 0.895 \mathrm{~mm}$ ) WL-CSP package.

Figure 26:
8-bump WL-CSP with 0.4 mm Pitch


## Note(s):

1. ccc Coplanarity.
2. All dimensions in $\mu \mathrm{m}$.

Figure 27:
Package Marking

| Tracecode | Marking Code |
| :---: | :---: |
| $X X X X$ | $z z$ |

Figure 28:
8 -pin (2x2) TDFN Package


Note(s):

1. Dimensions \& tolerancing conform to ASME Y14.5M-1994.
2. All dimensions are in millimeters. Angles are in degrees.
3. Coplanarity applies to the terminal.
4. Radius on terminal is optional.
5. N is the total number of terminals.

Figure 29:
Package Marking

| Trace Code | Marking Code |
| :---: | :---: |
| $X X X$ | $z z$ |

Ordering \& Contact Information

The device is available as the standard products listed in the table below.

On request, all devices can be factory set to enable a $100 \mathrm{k} \Omega$ pull-down resistor for the EN pin.

Figure 30:
Ordering Information

| Ordering Code | Package | Marking | ILIMIT | Output | Delivery Form | Delivery Quantity |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| AS1345A-BWLT-AD | 8-balls WL-CSP | BK | 100 mA | Adj. | Tape \& Reel | 1000 pcs/reel |
| AS1345A-BWLT-12 | 8-balls WL-CSP | BS | 100 mA | 1.2 V | Tape \& Reel | 1000 pcs/reel |
| AS1345A-BWLT-15 | 8-balls WL-CSP | CA | 100 mA | 1.5 V | Tape \& Reel | 1000 pcs/reel |
| AS1345A-BWLT-17 | 8-balls WL-CSP | Cl | 100 mA | 1.7V | Tape \& Reel | 1000 pcs/reel |
| AS1345B-BWLT-AD | 8-balls WL-CSP | CB | 200 mA | Adj. | Tape \& Reel | 1000 pcs/reel |
| AS1345D-BWLT-AD | 8-balls WL-CSP | BN | 500 mA | Adj. | Tape \& Reel | 1000 pcs/reel |
| AS1345D-BWLT-15 | 8-balls WL-CSP | BG | 500mA | 1.5 V | Tape \& Reel | 1000 pcs/reel |
| AS1345D-BWLT-17 | 8-balls WL-CSP | BH | 500mA | 1.7V | Tape \& Reel | 1000 pcs/reel |
| AS1345A-BTDT-AD | 8-pin TDFN | BI | 100mA | Adj. | Tape \& Reel | 1000 pcs/reel |
| AS1345B-BTDT-AD | 8-pin TDFN | BJ | 200mA | Adj. | Tape \& Reel | 1000 pcs/reel |
| AS1345C-BTDT-AD | 8-pin TDFN | CD | 350 mA | Adj. | Tape \& Reel | 1000 pcs/reel |
| AS1345D-BTDT-AD | 8-pin TDFN | CL | 500mA | Adj. | Tape \& Reel | 1000 pcs/reel |

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## Headquarters

ams AG
Tobelbader Strasse 30
8141 Premstaetten
Austria, Europe

Tel: +43 (0) 31365000
Website: www.ams.com

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## Document Status

| Document Status | Product Status | Definition |
| :---: | :--- | :--- |
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|  |  |  |

## Revision Information

Changes from 1-55 (2015-Apr-29) to current revision 1-56 (2016-Dec-28) Page

Updated Figure 30

## Note(s):

1. Page and figure numbers for the previous version may differ from page and figure numbers in the current revision.
2. Correction of typographical errors is not explicitly mentioned.

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